1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-30153-B.

2. Structure :

2-1. Planar type : PIN diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy.
Back side (Cathode) : Gold.

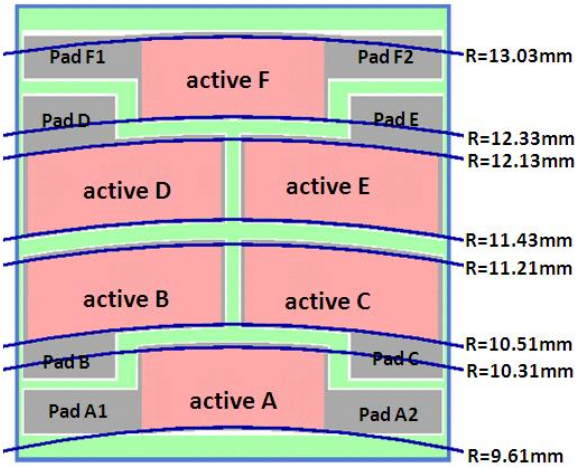
3. Size :

3-1. Chip size (including scribe line) : 3.80 mm × 4.00 mm.
3-2. Chip thickness : 0.305 mm ± 0.025 mm.
3-3. Active area :
A : 1.60 mm x 0.70 mm ; R_1=9.61mm, R_2=10.31mm.
B & C : 1.70 mm x 0.70 mm ; R_1=10.51mm, R_2=11.21mm.
D & E : 1.70 mm x 0.70 mm ; R_1=11.43mm, R_2=12.13mm.
F : 1.60 mm x 0.70 mm ; R_1=12.33mm, R_2=13.03mm.
3-4. Bonding pad (Anode) : A1 & A2 : 1.005 mm x 0.37 mm.
B & C : 0.795 mm x 0.282 mm.
D & E : 0.795 mm x 0.404 mm.
F1 & F2 : 0.990 mm x 0.370 mm.
3-5. Pattern drawing : refer to the attached drawing.

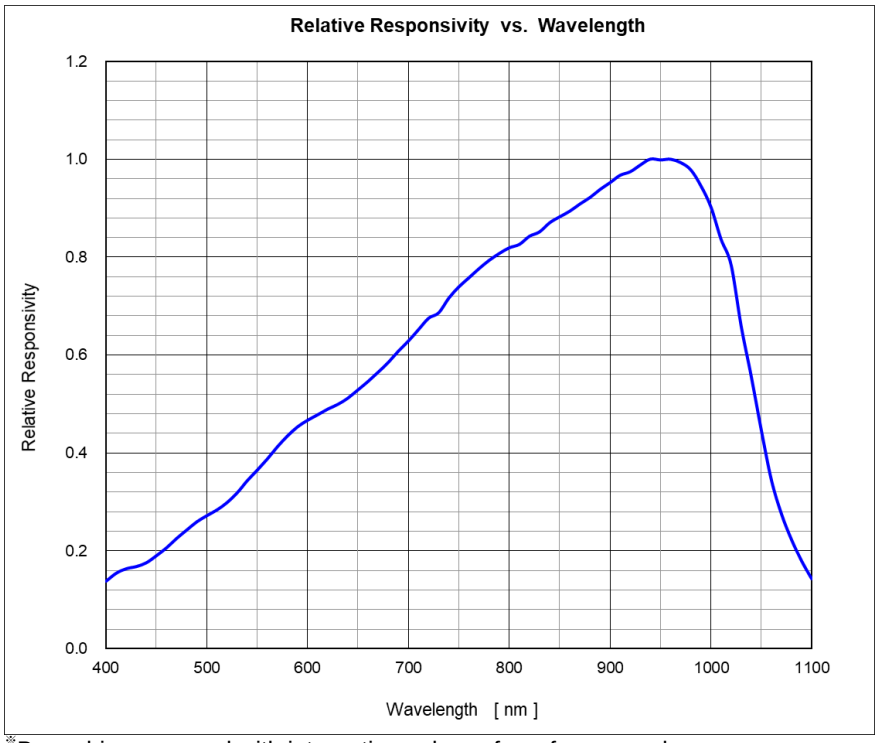
4. Electro-optical characteristics_ one chip (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse dark Current	I_D	V_R=20V Ee=0mW/cm²			10	nA
※Reverse breakdown voltage	$V_{(BR)R}$	I_R=100uA Ee=0mW/cm²	60			V
※Forward Voltage	V_F	I_F=20mA Ee=0mW/cm²			1.2	V
Open circuit Voltage	Voc	T=2856K Ee=5mW/cm²		395		mV
Total Capacitance	C_t	V_R =5V Ee=0mW/cm² f=1MHz		9		pF

※Based on 100% probing



5. Relative spectral responsivity



※Bare chip measured with integrating sphere, for reference only.